

# 4V Drive Pch MOSFET

## RP1E100RP

### ● Structure

Silicon P-channel MOSFET

### ● Features

- 1) Low On-resistance.
- 2) High power package.
- 3) 4V drive.

### ● Application

Switching

### ● Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	1000
RP1E100RP		○

### ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{DSS}$	-30	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	Continuous	$I_D$	$\pm 10$	A
	Pulsed	$I_{DP}$ *1	$\pm 40$	A
Source current (Body Diode)	Continuous	$I_S$	-1.6	A
	Pulsed	$I_{SP}$ *1	-40	A
Power dissipation		$P_D$ *2	2.0	W
Channel temperature		$T_{ch}$	150	°C
Range of storage temperature		$T_{stg}$	-55 to +150	°C

 \*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$ 

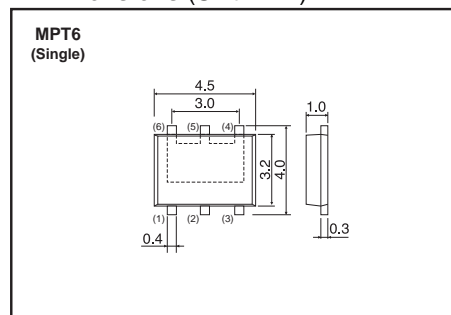
\*2 Mounted on a ceramic board.

### ● Thermal resistance

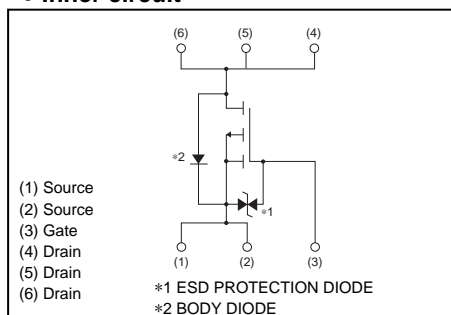
Parameter	Symbol	Limits	Unit
Channel to Ambient	$R_{th(ch-a)}$ *	62.5	°C / W

\*Mounted on a ceramic board.

### ● Dimensions (Unit : mm)



### ● Inner circuit



## ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	$\pm 10$	$\mu A$	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$I_D = -1mA, V_{GS} = 0V$
Zero gate voltage drain current	$I_{DSS}$	-	-	-1	$\mu A$	$V_{DS} = -30V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	-1.0	-	-2.5	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	9.0	12.6	m $\Omega$	$I_D = -10A, V_{GS} = -10V$
		-	12.5	17.5		$I_D = -5A, V_{GS} = -4.5V$
		-	14.0	19.6		$I_D = -5A, V_{GS} = -4.0V$
Forward transfer admittance	$ Y_{fs} ^*$	13	-	-	S	$I_D = -10A, V_{DS} = -10V$
Input capacitance	$C_{iss}$	-	3600	-	pF	$V_{DS} = -10V$
Output capacitance	$C_{oss}$	-	450	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	$C_{rss}$	-	450	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	25	-	ns	$I_D = -5A, V_{DD} = -15V$
Rise time	$t_r^*$	-	60	-	ns	$V_{GS} = -10V$
Turn-off delay time	$t_{d(off)}^*$	-	150	-	ns	$R_L = 3.0\Omega$
Fall time	$t_f^*$	-	100	-	ns	$R_G = 10\Omega$
Total gate charge	$Q_g^*$	-	39	-	nC	$I_D = -10A, V_{DD} = -15V$
Gate-source charge	$Q_{gs}^*$	-	8.5	-	nC	$V_{GS} = -5V, R_L = 1.5\Omega$
Gate-drain charge	$Q_{gd}^*$	-	13.5	-	nC	$R_G = 10\Omega$

\*Pulsed

## ● Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	$V_{SD}^*$	-	-	-1.2	V	$I_S = -10A, V_{GS} = 0V$

\*Pulsed

● Electrical characteristic curves

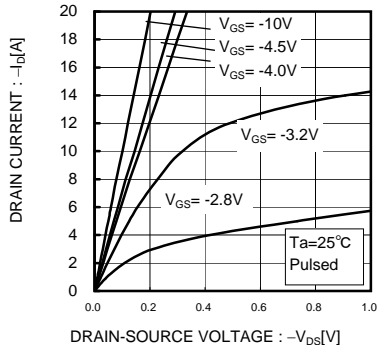


Fig.1 Typical output characteristics ( I )

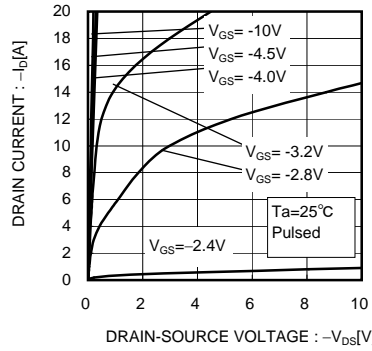


Fig.2 Typical output characteristics ( II )

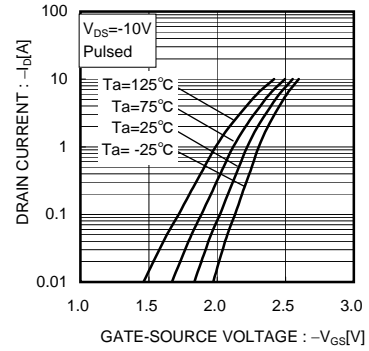


Fig.3 Typical Transfer Characteristics

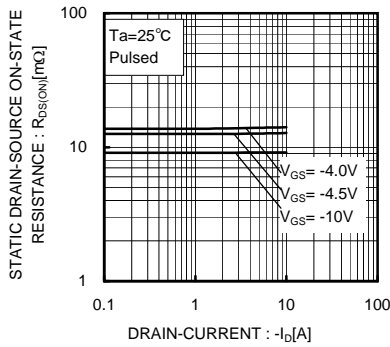


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current ( I )

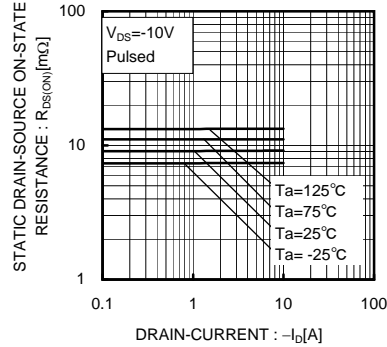


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current ( II )

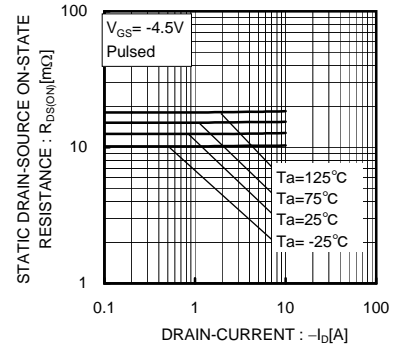


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current ( III )

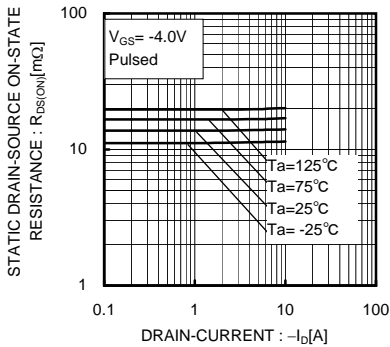


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current

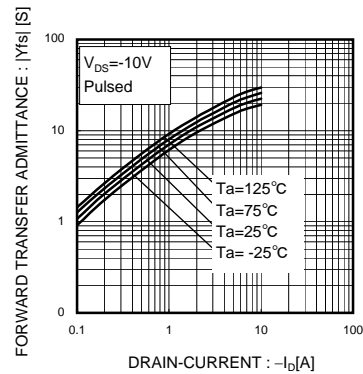


Fig.8 Forward Transfer Admittance vs. Drain Current

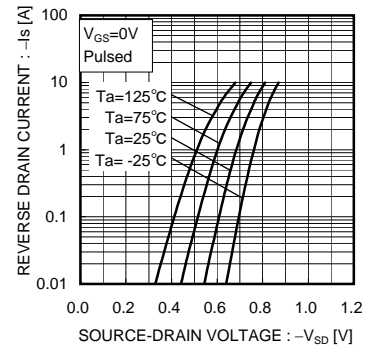


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

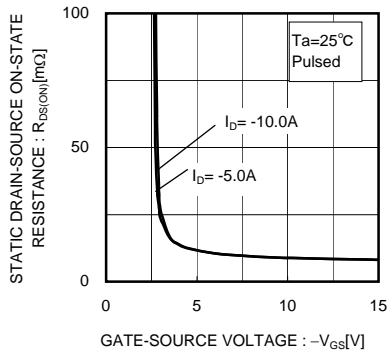


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

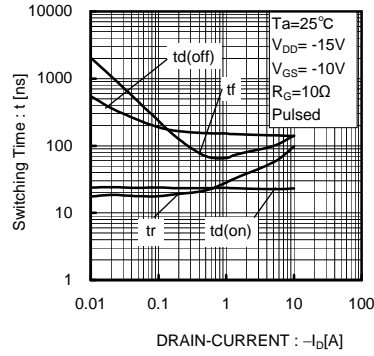


Fig.11 Switching Characteristics

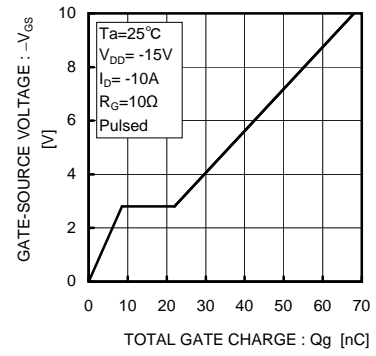


Fig.12 Dynamic Input Characteristics

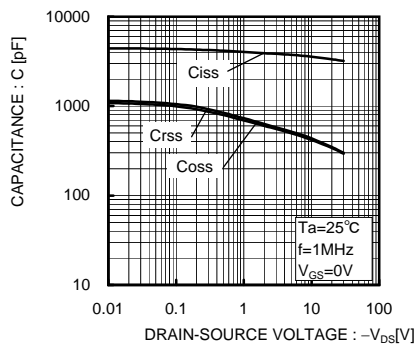


Fig.13 Typical Capacitance vs. Drain-Source Voltage

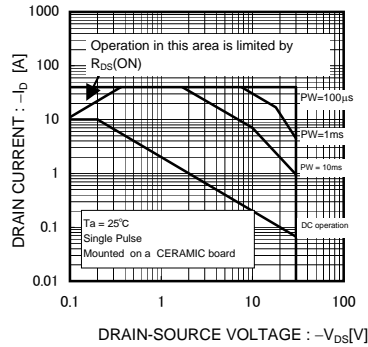


Fig.14 Maximum Safe Operating Area

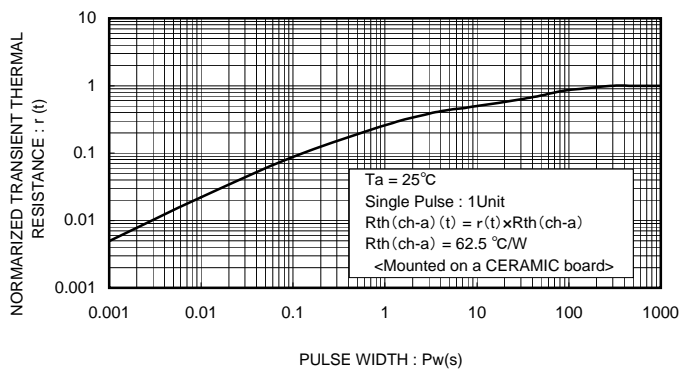


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

● Measurement circuits

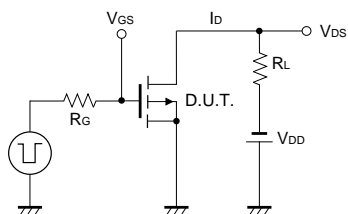


Fig.1-1 Switching Time Measurement Circuit

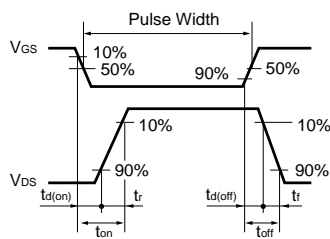


Fig.1-2 Switching Waveforms

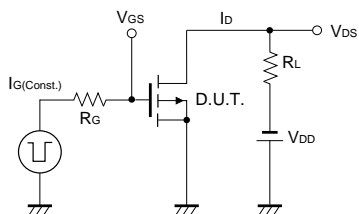


Fig.2-1 Gate Charge Measurement Circuit

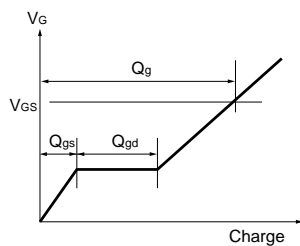


Fig.2-2 Gate Charge Waveform

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